

MPSA75

MPSA76

MPSA77

CASE 29-02, STYLE 1
TO-92 (TO-226AA)

DARLINGTON TRANSISTOR

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	MPSA75	MPSA76	MPSA77	Unit
Collector-Emitter Voltage	V _{CES}	40	50	60	Vdc
Emitter-Base Voltage	V _{EBO}		10		Vdc
Collector Current — Continuous	I _C		500		mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D		625	5.0	mW mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}		-55 to + 150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	R _{θJA}	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

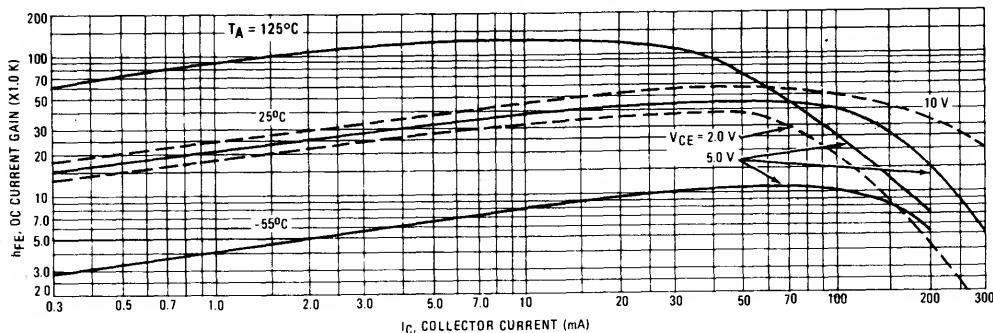
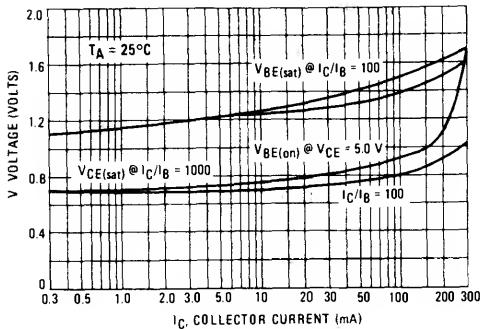
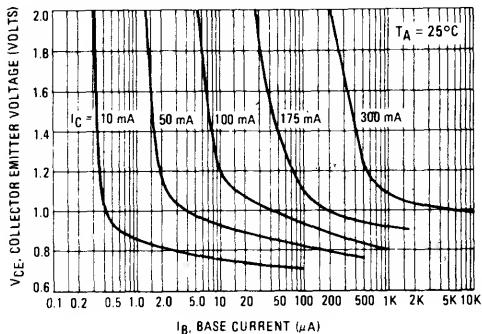
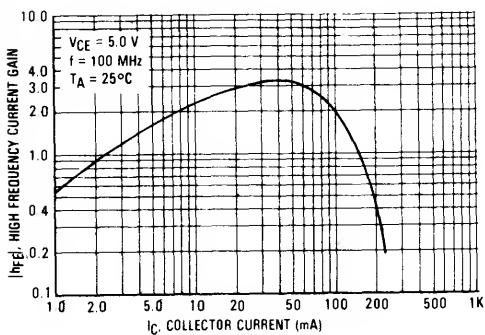
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I _C = 100 μAdc, V _{BE} = 0)	V(BR)CES	40	—	—	Vdc
		50	—	—	
		60	—	—	
Collector-Base Breakdown Voltage (I _C = 100 μAdc, I _E = 0)	V(BR)CBO	40	—	—	Vdc
		50	—	—	
		60	—	—	
Collector Cutoff Current (V _{CB} = 30 V, I _E = 0) (V _{CB} = 40 V, I _E = 0) (V _{CB} = 50 V, I _E = 0)	I _{CBO}	—	—	100	nAdc
		—	—	100	
		—	—	100	
Collector Cutoff Current (V _{CE} = 30 V, V _{BE} = 0) (V _{CE} = 40 V, V _{BE} = 0) (V _{CE} = 50 V, V _{BE} = 0)	I _{CES}	—	—	500	nAdc
		—	—	500	
		—	—	500	
Emitter Cutoff Current (V _{BE} = 10 Vdc)	I _{EBO}	—	—	100	nAdc

ON CHARACTERISTICS

DC Current Gain (I _C = 10 mA, V _{CE} = 5.0 V) (I _C = 100 mA, V _{CE} = 5.0 V)	h _{FE}	10,000 10,000	—	—	—
Collector-Emitter Saturation Voltage (I _C = 100 mA, I _B = 0.1 mA)	V _{CE(sat)}	—	—	1.5	Vdc
Base-Emitter On Voltage (I _C = 100 mA, V _{CE} = 5.0 Vdc)	V _{BE}	—	—	2.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current Gain — High Frequency (I _C = 10 mA, V _{CE} = 5.0 V, f = 100 MHz)	h _{fe}	1.25	2.4	—	—
---	-----------------	------	-----	---	---

MPSA75, MPSA76, MPSA77
FIGURE 1 — DC CURRENT GAIN

FIGURE 2 — "ON" VOLTAGE

FIGURE 3 — COLLECTOR SATURATION REGION

FIGURE 4 — HIGH FREQUENCY CURRENT GAIN

FIGURE 5 — ACTIVE REGION, SAFE OPERATING AREA
